



SRAM MODULE 1Mbyte (256K x 32-Bit) 3.3V, 68-Pin JLCC Packaging
 Part No. HMS25632J2V

GENERAL DESCRIPTION

The HMS25632J2V is a high-speed static random access memory (SRAM) module containing 262,144 words organized in a x32-bit configuration. The module consists of two 256K x 16 SRAMs mounted on a 68-pin, double-sided, FR4-printed circuit board. The HMS25632J2V uses 31 common input and output lines and has an output enable pin which operates faster than address access time at read cycle. Also it allows that lower and upper byte access by data byte control (/BS0~/BS3). Output enable (/OE) and write enable (/WE) can set the memory input and output. Data is written into the SRAM memory when write enable (/WE) and chip enable (/CE) inputs are both LOW. Reading is accomplished when /WE remains HIGH and /CE and output enable (/OE) are LOW. For reliability, this SRAM module is designed as multiple power and ground pin. All module components may be powered from a single +3.3V DC power supply and all inputs and outputs are fully LVTTTL-compatible.

FEATURES

- w Access times : 10, 12, 15, and 70, 85, 100ns
- w Low Power Dissipation
- w High-density 1Mbyte design
- w High-reliability, high-speed design
- w Single + 3.3V ±0.3V power supply
- w Easy memory expansion /CE and /OE functions
- w All inputs and outputs are LVTTTL-compatible
- w Industry-standard pinout
- w FR4-PCB design
- w Low profile 68-pin JLCC

OPTIONS

- w Timing
- 10ns access
- 12ns access
- 15ns access

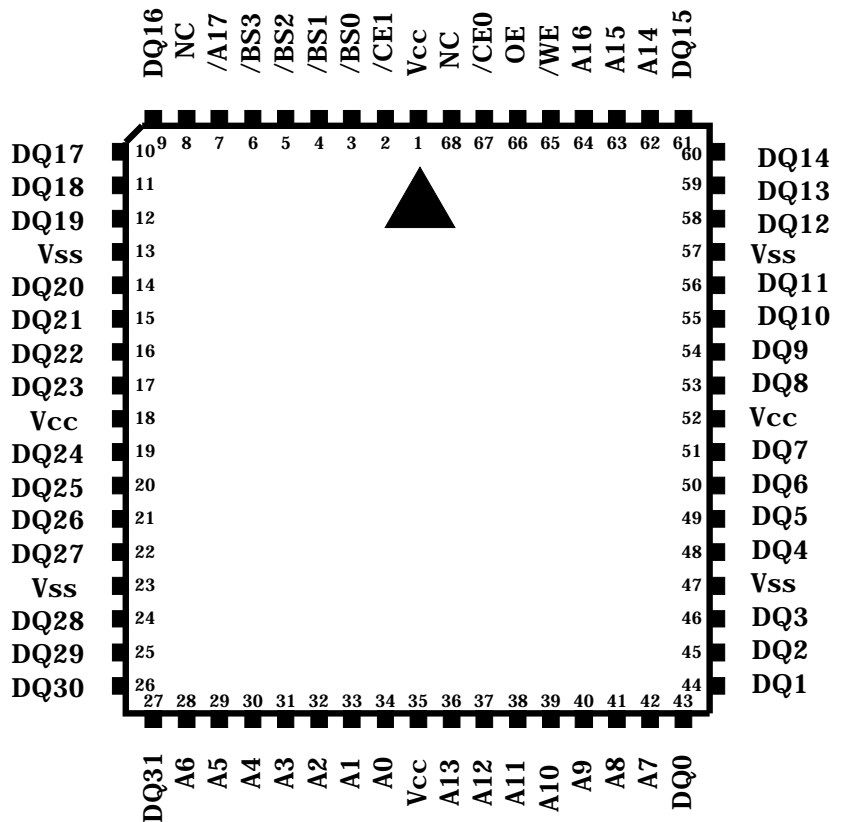
MARKING

- 10
- 12
- 15

w Packages

- 68-pin JLCC J

PIN ASSIGNMENT

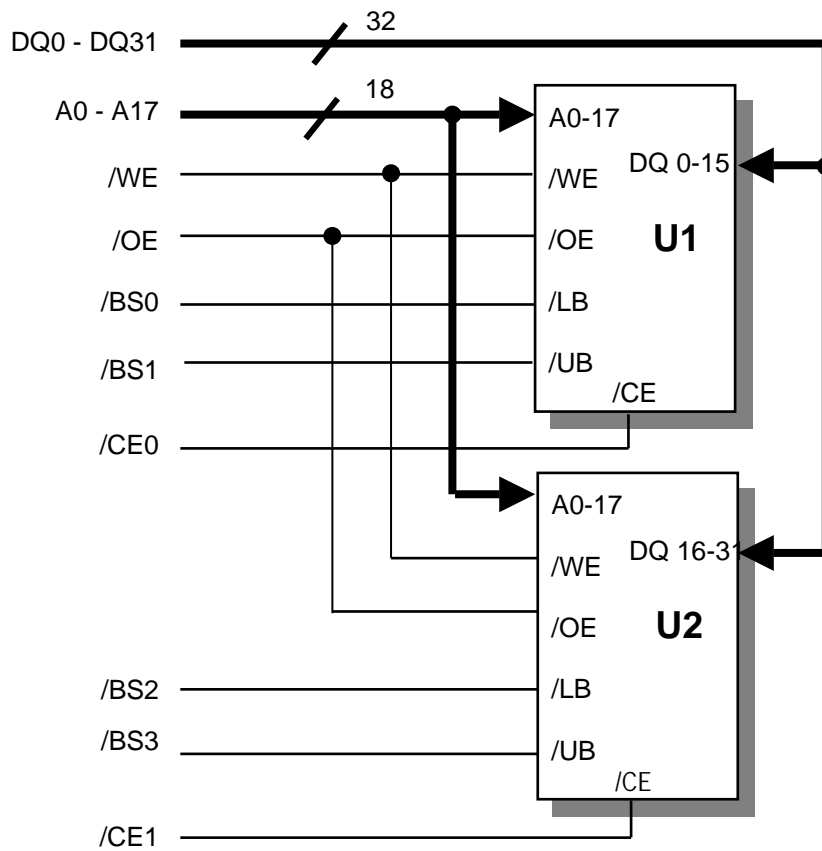


JLCC TOP VIEW

PIN FUNCTION

PIN NAME	PIN FUNCTION	PIN NAME	PIN FUNCTION
A0-A17	Address Inputs	/BS0 ~ /BS3	Byte Controls
DQ0-31	Data Inputs	Vcc	Power(+3.3V)
/WE	Write Enable	Vss	Ground
/CE	Chip Enable	N.C	No Connection
/OE	Output Enable		

FUNCTIONAL BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATING
Voltage on Any Pin Relative to V _{SS}		V _{IN,OUT}	-0.5V to +4.6V
Voltage on V _{CC} Supply Relative to V _{SS}		V _{CC}	-0.5V to +4.6V
Power Dissipation		P _D	2W
Storage Temperature		T _{STG}	-65°C to +150°C
Operating Temperature	Commercial	T _A	0°C to +70°C
	Industrial	T _A	-40°C to +85°C

w Stresses greater than those listed under " Absolute Maximum Ratings" may cause permanent damage to the device.

This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operating section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS (T_A=0 to 70 ° C)

PARAMETER	SYMBOL	MIN	TYP.	MAX
Supply Voltage	V _{CC}	3.0V	3.3V	3.6V
Ground	V _{SS}	0	0	0
Input High Voltage	V _{IH}	2.0	-	V _{CC} +0.3V**
Input Low Voltage	V _{IL}	-0.3*	-	0.8V

* V_{IL}(Min.) = -2.0V (Pulse Width ≤ 10ns) for I ≤ 20 mA

** V_{IH}(Min.) = V_{CC}+2.0V (Pulse Width ≤ 10ns) for I ≤ 20 mA

DC AND OPERATING CHARACTERISTICS (1)

(0°C ≤ T_A ≤ 70 °C ; V_{CC} = 3.3V ± 0.3V, Unless otherwise specified)

PARAMETER	TEST CONDITIONS	SYMBOL	MIN	MAX	UNITS
Input Leakage Current	V _{IN} = V _{SS} to V _{CC}	I _{L1}	-4	4	μA
Output Leakage Current	/CE=V _{IH} or /OE =V _{IH} or /WE=V _{IL} V _{OUT} =V _{SS} to V _{CC}	I _{L0}	-4	4	μA
Output High Voltage	I _{OH} = -4.0mA	V _{OH}	2.4		V
Output Low Voltage	I _{OL} = 8.0mA	V _{OL}		0.4	V

* V_{CC}=3.3V, Temp=25 °C

DC AND OPERATING CHARACTERISTICS (2)

DESCRIPTION	TEST CONDITIONS	SYMBOL	MAX			UNIT
			-10	-12	-15	
Power Supply Current:Operating	Min. Cycle, 100% Duty /CE=V _{IL} , V _{IN} =V _{IH} or V _{IL} , I _{OUT} =0mA	I _{CC}	500	490	480	mA
Power Supply Current:Standby	Min. Cycle, /CE=V _{IH}	I _{SB}	100	100	100	mA
	f=0MHZ, /CE≥V _{CC} -0.2V, V _{IN} ≥ V _{CC} -0.2V or V _{IN} ≤0.2V	I _{SB1}	20	20	20	mA

CAPACITANCE

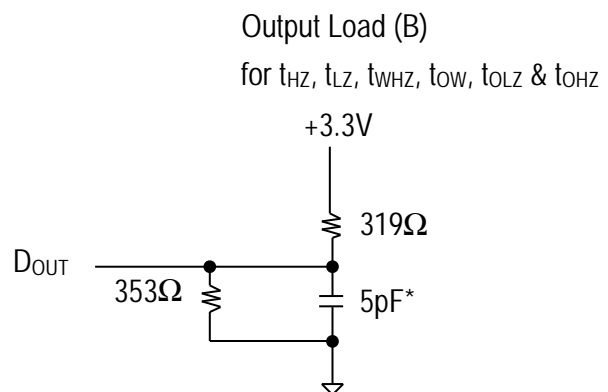
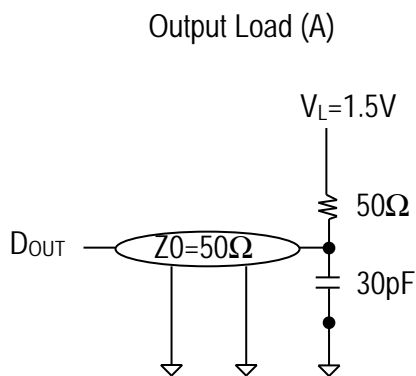
DESCRIPTION	TEST CONDITIONS	SYMBOL	MAX	UNIT
Input /Output Capacitance	V _{I/O} =0V	C _{I/O}	16	pF
Input Capacitance	V _{IN} =0V	C _{IN}	14	pF

* NOTE: Capacitance is sampled and not 100% tested

AC CHARACTERISTICS (0°C ≤ T_A ≤ 70 °C ; V_{CC} = 3.3V ± 0.3V, unless otherwise specified)

TEST CONDITIONS

PARAMETER	VALUE
Input Pulse Level	0 to 3V
Input Rise and Fall Time	3ns
Input and Output Timing Reference Levels	1.5V
Output Load	See below



READ CYCLE

PARAMETER	SYMBOL	-10		-12		-15		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
Read Cycle Time	t_{RC}	10	-	12	-	15	-	ns
Address Access Time	t_{AA}	-	10	-	12	-	15	ns
Chip Select to Output	t_{CO}	-	10	-	12	-	15	ns
Output Enable to Valid Output	t_{OE}	-	5	-	6	-	7	ns
/BS0 ~ /BS3 Access Time	t_{BA}	-	5	-	6	-	7	ns
Chip Enable to Low-Z Output	t_{LZ}	3	-	3	-	3	-	ns
Output Enable to Low-Z Output	t_{OLZ}	0	-	0	-	0	-	ns
/BS0 ~ /BS3 Enable to Low-Z Output	t_{BHZ}	0	-	0	-	0	-	ns
Chip Disable to High-Z Output	t_{HZ}	0	5	3	6	0	7	ns
Output Disable to High-Z Output	t_{OHZ}	0	5	0	6	0	7	
/BS0 ~ /BS3 Disable to High-Z Output	t_{BHZ}	0	5	0	6	0	7	ns
Output Hold from address Change	t_{OH}	3	-	3	-	3	-	ns

WRITE CYCLE

PARAMETER	SYMBOL	-10		-12		-15		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
Write Cycle Time	t_{WC}	10	-	12	-	15	-	ns
Chip Select to End of Write	t_{CW}	7	-	8	-	10	-	ns
Address Set-up Time	t_{AS}	0	-	0	-	0	-	ns
Address Valid to End of Write	t_{AW}	7	-	8	-	10	-	ns
Write Pulse Width (/OE High)	t_{WP}	7	-	8	-	10	-	ns
Write Pulse Width (/OE Low)	t_{WP1}	10	-	12	-	15	-	ns
Write Recovery Time	t_{WR}	0	-	0	-	0	-	ns
Write to Output High-Z	t_{WHZ}	0	5	0	6	0	7	ns
Data to Write Time Overlap	t_{DW}	5	-	6	-	7	-	ns
Data Hold from Write Time	t_{DH}	0	-	0	-	0	-	ns
End of Write to Output Low-Z	t_{OW}	3	-	3	-	3	-	ns

TIMING DIAGRAMS

See Part No. HMS25632J2

FUNCTIONAL DESCRIPTION

/CE	/WE	/OE	MODE	I/O PIN	SUPPLY CURRENT
H	X*	X	Not Select	High-Z	I_{SB}, I_{SB1}
L	H	H	Output Disable	High-Z	I_{CC}
L	H	L	Read	D_{OUT}	I_{CC}
L	L	X	Write	D_{IN}	I_{CC}

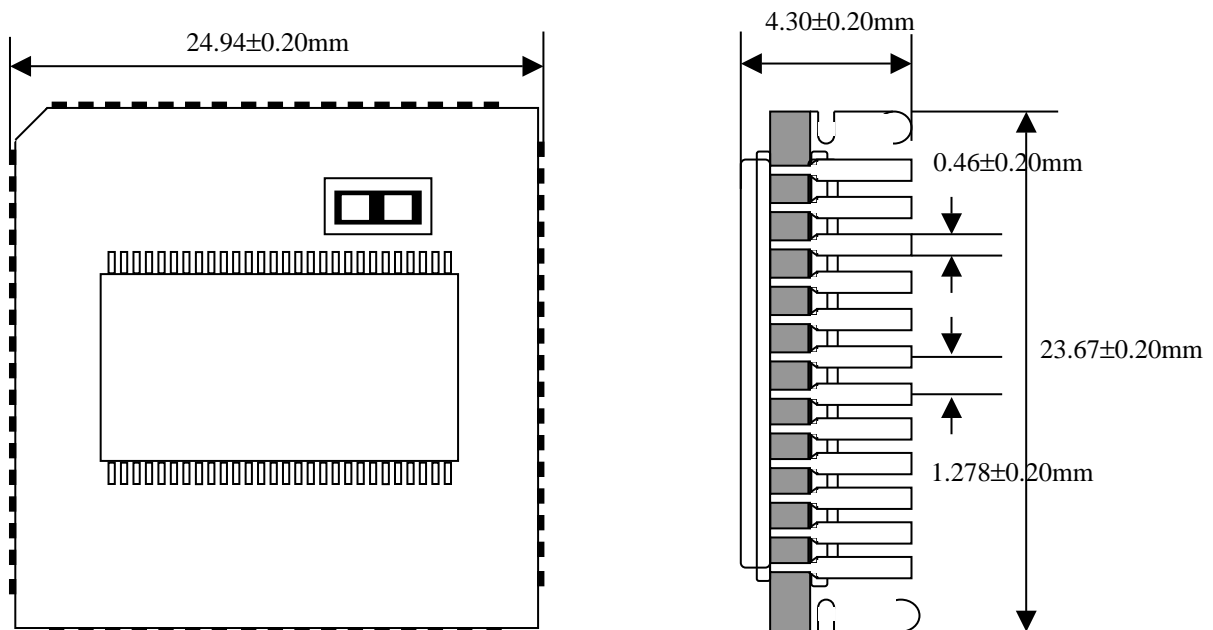
Note: X means Don't Care

DATA RETENTION CHARACTERISTICS* ($T_A = 0$ to 70 °C)

PARAMETER	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
V_{CC} for Data Retention	V_{DR}	$/CE \geq V_{CC}-0.2V$	2.0	3.6	V
Data Retention Current	I_{DR}	$V_{CC}=3.0V, /CE \geq V_{CC}-0.2V$ $V_{IN} \geq V_{CC}-0.2V$ or $V_{IN} \leq 0.2V$	-	2.0	mA
Data Retention Set-up Time	t_{SDR}	See Data Retention Wave forms(below)	0	-	ns
Recovery Time	t_{RDR}		5	-	ns

* L-Version Only

PACKAGING DIMENSIONS



ORDERING INFORMATION

Part Number	Density	Org.	Package	Function	Vcc	Access Time
HMS25632J2V-10	1MByte	256KX 32bit	68 Pin-JLCC	Low power	3.3V	10ns
HMS25632J2V-12	1MByte	256KX 32bit	68 Pin-JLCC	Low power	3.3V	12ns
HMS25632J2V-15	1MByte	256KX 32bit	68 Pin-JLCC	Low power	3.3V	15ns
HMS25632J2V-70	1MByte	256KX 32bit	68 Pin-JLCC	Low power	3.3V	70ns
HMS25632J2V-85	1MByte	256KX 32bit	68 Pin-JLCC	Low power	3.3V	85ns
HMS25632J2V-100	1MByte	256KX 32bit	68 Pin-JLCC	Low power	3.3V	100ns